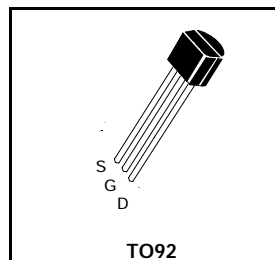


N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2- NOVEMBER 94

2N7000



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	V_{CES}	60	V
Continuous Drain Current	I_D	0.2	A
Pulsed Drain Current	I_{DM}	0.5	A
Gate Source Voltage	V_{GS}	± 40	V
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	400	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	60		V	$I_D=10\mu\text{A}, V_{GS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	3.0	V	$I_D=1\text{mA}, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		10	nA	$V_{GS}=\pm 15\text{V}, V_{DS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}		1 1	μA mA	$V_{DS}=48\text{V}, V_{GS}=0$ $V_{DS}=48\text{V}, V_{GS}=0\text{V}, T=125^\circ\text{C}(2)$
On-State Drain Current(1)	$I_{D(on)}$	75		mA	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}$
Static Drain-Source On-State Voltage (1)	$V_{DS(on)}$		2.5 0.4	V V	$V_{GS}=10\text{V}, I_D=500\text{mA}$ $V_{GS}=4.5\text{V}, I_D=75\text{mA}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		5	Ω	$V_{GS}=10\text{V}, I_D=500\text{mA}$
Forward Transconductance(1)(2)	g_{fs}	100		mS	$V_{DS}=10\text{V}, I_D=200\text{mA}$
Input Capacitance (2)	C_{iss}		60	pF	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$
Common Source Output Capacitance (2)	C_{oss}		25	pF	
Reverse Transfer Capacitance (2)	C_{rss}		5	pF	
Turn-On Time (2)(3)	$t_{(on)}$		10	ns	$V_{DD}=15\text{V}, I_D=500\text{mA}$ $R_g=25\Omega, R_L=25\Omega$
Turn-Off Time (2)(3)	$t_{(off)}$		10	ns	

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$ (2) Sample test.

(3) Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator